**AMMPLEON** 

Product data sheet

#### **Product profile** 1.

### 1.1 General description

A 1200 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 500 MHz band.

Table 1. **Application information** 

Mode of operation	f	V <sub>DS</sub>	$P_L$	G <sub>p</sub>	$\eta_D$
	(MHz)	(V)	(W)	(dB)	(%)
CW	108	50	1000	26	75
pulsed RF	225	50	1200	24	71

#### 1.2 Features and benefits

- Typical pulsed performance at frequency of 225 MHz, a supply voltage of 50 V and an  $I_{Da}$  of 40 mA, a  $t_p$  of 100  $\mu$ s with  $\delta$  of 20 %:
  - ◆ Output power = 1200 W
  - ◆ Power gain = 24 dB
  - ◆ Efficiency = 71 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

**Power LDMOS transistor** 

# 2. Pinning information

Table 2. Pinning

drain1 drain2	1 2	_1
1 . 4	→	
gate1	5	3
gate2	3 4	5
source [1	1	4 7
		<b>'</b> ⊢¬
		2 sym117
	gate2	gate2 3 4

[1] Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	ame Description Version	
BLF578		flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	110	V
$V_{GS}$	gate-source voltage		-0.5	+11	V
I <sub>D</sub>	drain current		-	88	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

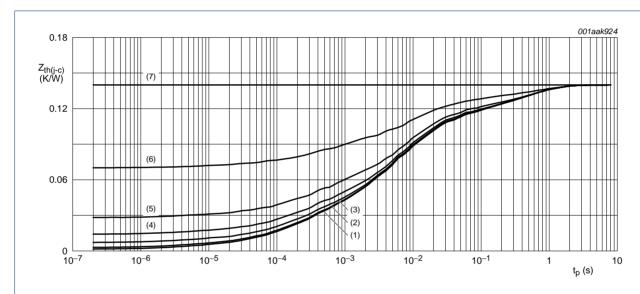
**Power LDMOS transistor** 

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_j = 150  ^{\circ}\text{C}$ [1][2]	0.14	K/W
Z <sub>th(j-c)</sub>	transient thermal impedance from junction to case	$T_j$ = 150 °C; $t_p$ = 100 $\mu$ s; $\delta$ = 20 %	0.04	K/W

- [1]  $T_i$  is the junction temperature.
- [2]  $R_{th(j-c)}$  is measured under RF conditions.
- [3] See Figure 1.



- (1)  $\delta = 1 \%$
- (2)  $\delta = 2 \%$
- (3)  $\delta = 5 \%$
- (4)  $\delta = 10 \%$
- (5)  $\delta = 20 \%$
- (6)  $\delta = 50 \%$
- (7)  $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as function of pulse duration

### 6. Characteristics

Table 6. DC characteristics

 $T_j$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.5 \text{ mA}$	110	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 500 mA	1.25	1.7	2.25	٧
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 20 \text{ mA}$	0.8	1.3	1.8	٧
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	2.8	μΑ

### **Power LDMOS transistor**

Table 6. DC characteristics ...continued

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	58	70	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 16.66 \text{ A}$	-	0.07	-	Ω
C <sub>rs</sub>	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	3	-	pF
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	403	-	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	138	-	pF

#### Table 7. RF characteristics

Mode of operation: pulsed RF;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %; f = 225 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Da}$  = 40 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G <sub>p</sub>	power gain	P <sub>L</sub> = 1200 W	23	24	25.4	dB
RLin	input return loss	P <sub>L</sub> = 1200 W	14	17.5	-	dB
$\eta_{D}$	drain efficiency	P <sub>L</sub> = 1200 W	68	71	-	%

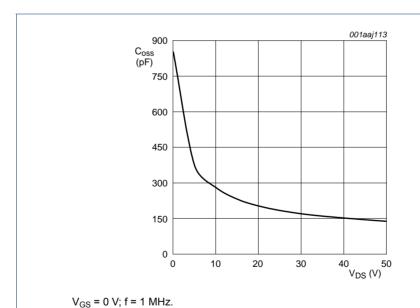


Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

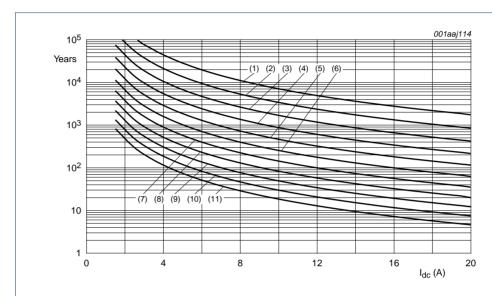
### 6.1 Ruggedness in class-AB operation

The BLF578 is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 40 mA;  $P_{L}$  = 1200 W pulsed; f = 225 MHz.

**Power LDMOS transistor** 

# 7. Application information

### 7.1 Reliability



TTF (0.1 % failure fraction).

The reliability at pulsed conditions can be calculated as follows: TTF (0.1 %)  $\times$  1/  $\delta$ .

- (1)  $T_i = 100 \, ^{\circ}C$
- (2)  $T_j = 110 \, ^{\circ}C$
- (3)  $T_j = 120 \, ^{\circ}C$
- (4)  $T_i = 130 \, ^{\circ}C$
- (5)  $T_j = 140 \, ^{\circ}\text{C}$
- (6)  $T_j = 150 \, ^{\circ}C$
- (7)  $T_j = 160 \, ^{\circ}\text{C}$
- (8)  $T_i = 170 \, ^{\circ}\text{C}$
- (9) T<sub>j</sub> = 180 °C
- (10)  $T_j = 190 \, ^{\circ}C$
- (11)  $T_j = 200 \, ^{\circ}C$

Fig 3. BLF578 electromigration (I<sub>D</sub>, total device)

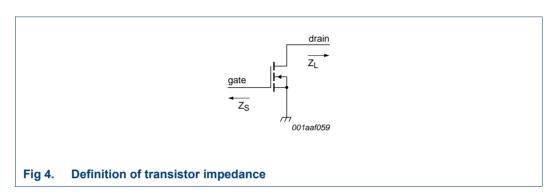
**Power LDMOS transistor** 

### 8. Test information

### 8.1 Impedance information

**Table 8. Typical impedance** Simulated  $Z_S$  and  $Z_L$  test circuit impedances.

f	Z <sub>S</sub>	Z <sub>L</sub>
MHz	Ω	Ω
225	3.2 + j2.6	3.7 – j0.2



### 8.2 RF performance

The following figures are measured in a class-AB production test circuit.

### 8.2.1 1-Tone CW pulsed

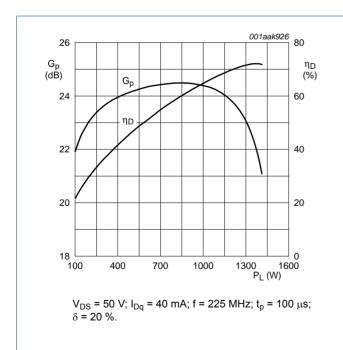
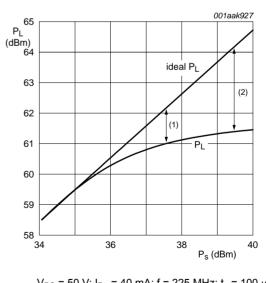


Fig 5. Power gain and drain efficiency as function of load power; typical values

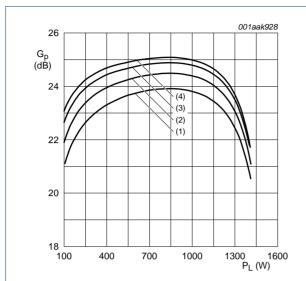


 $V_{DS}$  = 50 V;  $I_{Dq}$  = 40 mA; f = 225 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

- (1)  $P_{L(1dB)} = 61.0 \text{ dBm } (1260 \text{ W})$
- (2)  $P_{L(3dB)} = 61.4 \text{ dBm } (1400 \text{ W})$

Fig 6. Load Power as function of source power; typical values

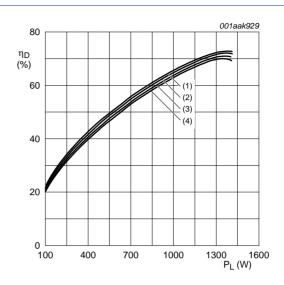
#### **Power LDMOS transistor**



 $V_{DS}$  = 50 V; f = 225 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $I_{Dq} = 0 \text{ mA}$
- (2)  $I_{Dq} = 40 \text{ mA}$
- (3)  $I_{Dq} = 80 \text{ mA}$
- (4)  $I_{Dq} = 160 \text{ mA}$

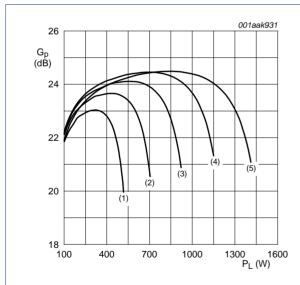
Fig 7. Power gain as a function of load power; typical values



 $V_{DS}$  = 50 V; f = 225 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $I_{Dq} = 0 \text{ mA}$
- (2)  $I_{Dq} = 40 \text{ mA}$
- (3)  $I_{Dq} = 80 \text{ mA}$
- (4)  $I_{Dq} = 160 \text{ mA}$

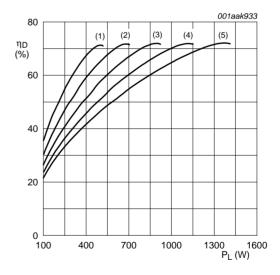
Fig 8. Drain efficiency as a function of load power; typical values



 $I_{Dq}$  = 40 mA; f = 225 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

- (1)  $V_{DS} = 30 \text{ V}$
- (2)  $V_{DS} = 35 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 45 \text{ V}$
- (5)  $V_{DS} = 50 \text{ V}$

Fig 9. Power gain as a function of load power; typical values



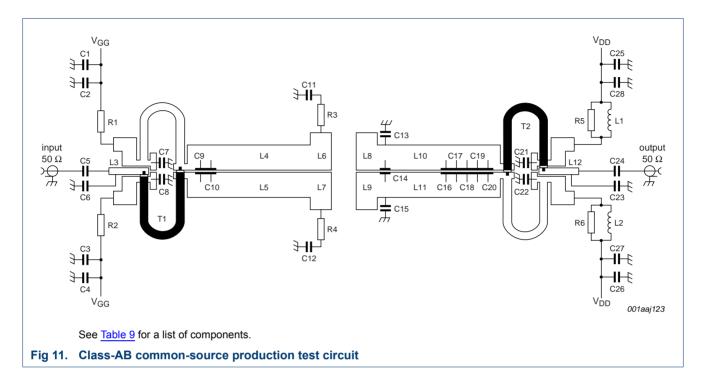
 $I_{Dq}$  = 40 mA; f = 225 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

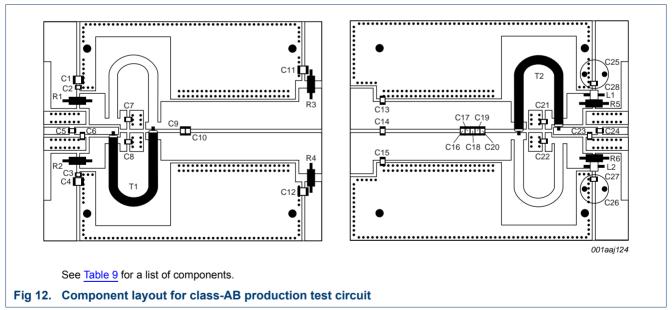
- (1)  $V_{DS} = 30 \text{ V}$
- (2)  $V_{DS} = 35 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 45 \text{ V}$
- (5)  $V_{DS} = 50 \text{ V}$

Fig 10. Drain efficiency as a function of load power; typical values

#### **Power LDMOS transistor**

### 8.3 Test circuit





### **Power LDMOS transistor**

Table 9. List of components

For production test circuit, see Figure 11 and Figure 12.

Printed-Circuit Board (PCB): Rogers 5880;  $\varepsilon_r = 2.2 \text{ F/m}$ ; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35  $\mu$ m.

Component	Description	Value	Remarks
C1, C2, C11, C12	multilayer ceramic chip capacitor	4.7 μF	TDK4532X7R1E475Mt020U
C2, C3, C27, C28	multilayer ceramic chip capacitor	100 nF	Murata X7R 250 V
C5, C7, C8, C21, C22	multilayer ceramic chip capacitor	1 nF [1]	
C6	multilayer ceramic chip capacitor	30 pF [1]	
C9, C10, C13, C15	multilayer ceramic chip capacitor	62 pF [1]	
C14	multilayer ceramic chip capacitor	36 pF [1]	
C16, C17	multilayer ceramic chip capacitor	24 pF [1]	
C18	multilayer ceramic chip capacitor	30 pF [1]	
C19	multilayer ceramic chip capacitor	27 pF [1]	
C20	multilayer ceramic chip capacitor	9.1 pF [1]	
C23	multilayer ceramic chip capacitor	13 pF [1]	
C24	multilayer ceramic chip capacitor	16 pF [1]	
C25, C26	electrolytic capacitor	220 μF; 63 V	
L1, L2	3 turns 1 mm copper wire	D = 2 mm; length = 3 mm	
L3, L12	stripline	-	(L × W) 15 mm × 2.4 mm
L4, L5, L10, L11	stripline	-	(L × W) 47 mm × 10 mm
L6, L7, L8, L9	stripline	-	(L × W) 8 mm × 15 mm
R1, R2	metal film resistor	2 Ω; 0.6 W	
R3, R4	metal film resistor	20 Ω; 0.6 W	
R5, R6	metal film resistor	1 Ω; 0.6 W	
T1, T2	semi rigid coax	50 Ω; 58 mm	EZ-141-AL-TP-M17

<sup>[1]</sup> American Technical Ceramics type 100B or capacitor of same quality.

**Power LDMOS transistor** 

## 9. Package outline

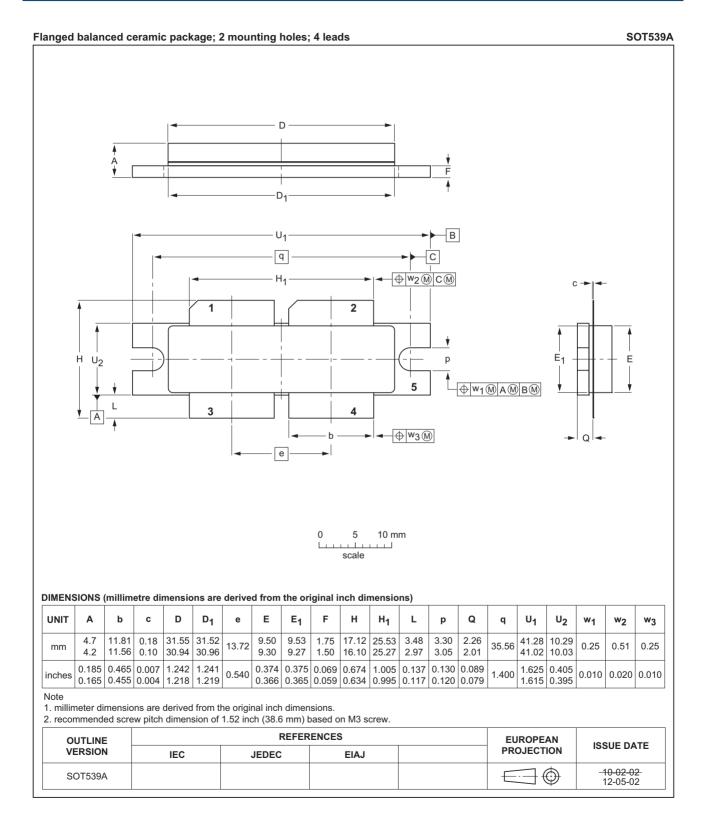


Fig 13. Package outline SOT539A

**Power LDMOS transistor** 

# 10. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

ESD model	Class
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [1]

<sup>[1]</sup> HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

### 11. Abbreviations

Table 11. Abbreviations

Acronym	Description
CW	Continuous Wave
EDGE	Enhanced Data rates for GSM Evolution
GSM	Global System for Mobile communications
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
TTF	Time To Failure
VSWR	Voltage Standing-Wave Ratio

# 12. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF578 v.4	20161201	Product data sheet	-	BLF578_3
Modifications:	Section 10 on page 11: updated Handling information			
BLF578_3	20150901	Product data sheet	-	BLF578_2
BLF578_2	20100204	Product data sheet	-	BLF578_1
BLF578_1	20081211	Objective data sheet	-	-

#### **Power LDMOS transistor**

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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